ABSTRACT

THERMAL PROCESSING EQUIPMENT CALIBRATION METHOD

The invention relates to a method for calibrating thermal processing equipment comprising a heating device and which is used for heat treatment of a multilayer substrate. To be able to optimize the calibration method while at the same time using cheaper material, the inventive method is characterized in comprising the steps: providing a test substrate with a different structure compared to the multilayer substrate, thermal processing of the test substrate using a set of thermal process parameters to thereby obtain a layer on the test substrate with a thickness profile, comparing the thickness profile with a predetermined thickness profile of a calibration layer on a calibration test substrate and amending the set of thermal process parameters such that the heating device is adapted to compensate the differences between the thickness profile and the predetermined thickness profile, wherein the predetermined thickness profile of the calibration layer on the calibration test substrate corresponds to an even thickness profile of a layer on a multilayer substrate both obtained with the same set of predetermined process conditions or to thermal process conditions for which reduced slip lines and/or reduced wafer deformation have been observed on the multilayer substrate. The invention also relates to a method for creating a calibration thickness profile and to a calibration test substrate comprising a thermally formed layer on one of its main surfaces with a predetermined thickness profile.